NPN SILICON RF TRANSISTOR

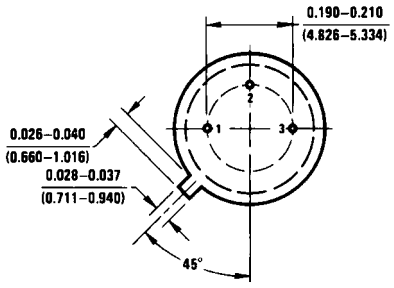
DESCRIPTION:

The **ASI 2N3553** is Designed for Amplifier, Oscillator and Driver Applications Covering VHF-UHF Frequency.

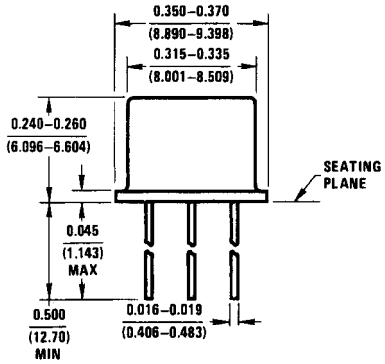
MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	40 V
P_{DISS}	7.0 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	25 ^{O}C/W

PACKAGE STYLE TO- 39



1 = EMITTER 2 = BASE
3 = COLLECTOR



CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 200 mA			40			V
I_{CEX}	V_{CE} = 65 V	V_{BE} = -1.5 V				1.0	mA
	V_{CE} = 30 V	V_{BE} = -1.5 V	T_C = 200 ^{O}C			5.0	
I_{CEO}	V_{CE} = 30 V					100	µA
I_{EBO}	V_{EB} = 4.0 V					100	µA
h_{FE}	V_{CE} = 5.0 V	I_C = 250 mA		10			---
$V_{CE(SAT)}$	I_C = 250 mA	I_B = 50 mA				1.0	V
C_{ob}	V_{CB} = 30 V		f = 1.0 MHz			10	pF
f_t	V_{CE} = 28 V	I_C = 100 mA	f = 100 MHz		500		MHz
P_{in}	V_{CE} = 28 V	P_{out} = 2.5 W	f = 175 MHz			250	mW
G_P				10			dB
η_C				50			%